TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

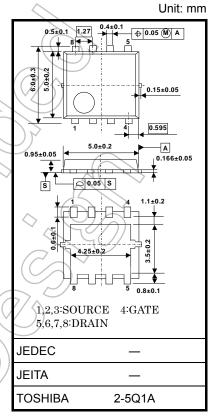
TPCA8028-H

High-Efficiency DC/DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- · High-speed switching
- Small gate charge: QSW = 20 nC (typ.)
- Low drain-source ON-resistance: RDS (ON) = $2.0 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 166 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode: $V_{th} = 1.3 \text{ to } 2.3 \text{ V (VDS} = 10 \text{ V, ID} = 1 \text{ mA)}$

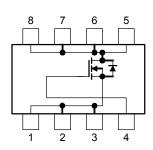
Absolute Maximum Ratings (Ta = 25°C)

			1	
Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	٧
Gate-source voltage		V _{GSS} <	±20	V
Drain current	DC (Note 1)	I _D	50	A
	Pulsed (Note 1)	I _{DP}	150	
Drain power dissipation	on (Tc=25°C)	PD PD	45	w
Drain power dissipation (t = 10 s) (Note 2a)		(PD)	2.8	M
Drain power dissipation $(t = 10 \text{ s})$ (Note 2b)		PD	1.6	w
Single-pulse avalanche energy (Note 3)		EAS	325	mJ
Avalanche current		I _{AR}	50	Α
Repetitive avalanche energy (Tc=25°C) (Note 4)		EAR	4.03	mJ
Channel temperature		Tch	150	°C
Storage temperature range		Tstg	-55 to 150	°C



Weight: 0.069 g (typ.)

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high

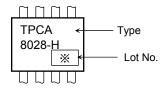
temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

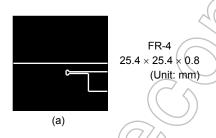
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R _{th (ch-a)}	78.1	°C/W

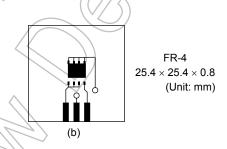
Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board





Note 3: $V_{DD} = 24 \text{ V}$, $T_{Ch} = 25 ^{\circ}\text{C}$ (initial), $L = 100 \ \mu\text{H}$, $R_G \neq 25 \ \Omega$, $I_{AR} = 50 \ \text{A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)

Week of manufacture

(01 for first week of year, continuing up to 52 or 53)

2

Year of manufacture

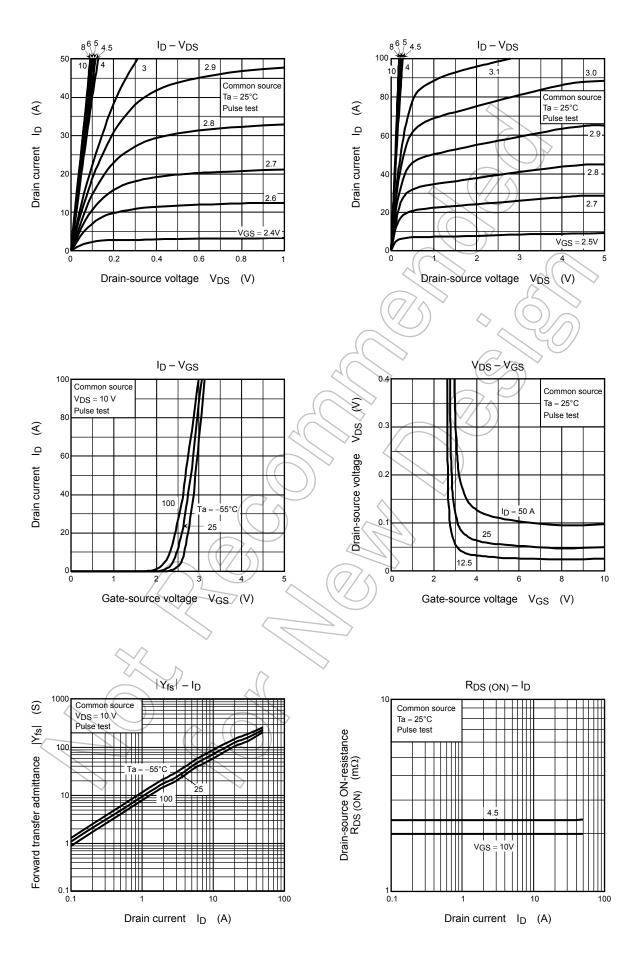
(The last digit of the calendar year)

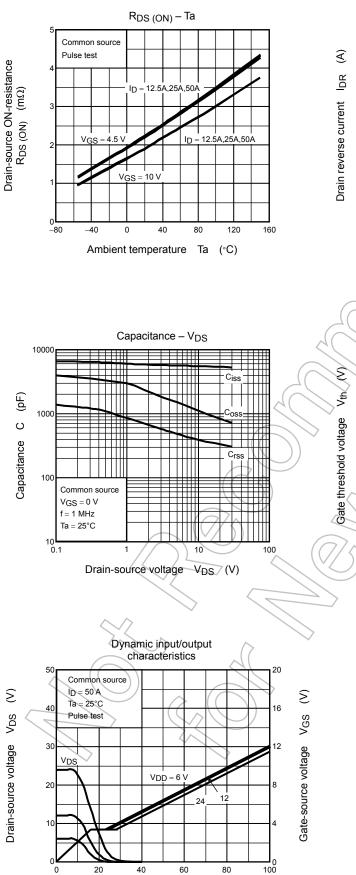
Electrical Characteristics (Ta = 25°C)

Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cutoff curre	nt	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	10	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	٧	
		V _{(BR) DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_		
Gate threshold vo	oltage	V_{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	1.3) /_	2.3	V	
Drain-source ON-resistance		R _{DS} (ON)	$V_{GS} = 4.5 \text{ V}, I_D = 25 \text{ A}$) _K	2.3	3.2	- mΩ	
			V _{GS} = 10 V, I _D = 25 A	\rightarrow	2.0	2.8		
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 25 A	83	166	_	S	
Input capacitance		C _{iss}			6000	7800		
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	380	610	pF	
Output capacitance		Coss			1100	\nearrow		
Gate resistance		Rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	1.0	1.5	Ω	
Switching time	Rise time	t _r	V _G S 10 V I _D = 25A O V _O UT G S 0 V O C S 0	M	5.0) _	ns	
	Turn-on time	t _{on}			16			
	Fall time	t _f	G.7.4 W O.8.		9.8		113	
	Turn-off time	t _{off}	V _{DD} ≃ 15 V Duty ≤ 1%, t _w = 10 μs		71	l		
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \simeq 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$		88			
			$V_{DD} \simeq 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 50 \text{ A}$	_	46	_		
Gate-source char	ge 1 (Q _{gs1}			16		nC	
Gate-drain ("Miller") charge		Q_{gd}	$V_{DD} \simeq 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$	_	12	_		
Gate switch charge		Q _{SW}		_	20	_		

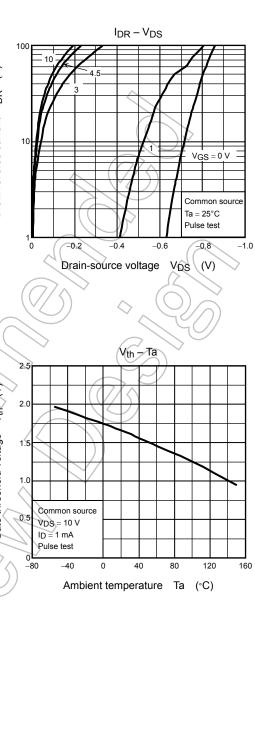
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I _{DRP}	> -	_	_	150	Α
Forward voltage (diode)	V _{DSF}	$I_{DR} = 50 \text{ A}, V_{GS} = 0 \text{ V}$		_	-1.2	V

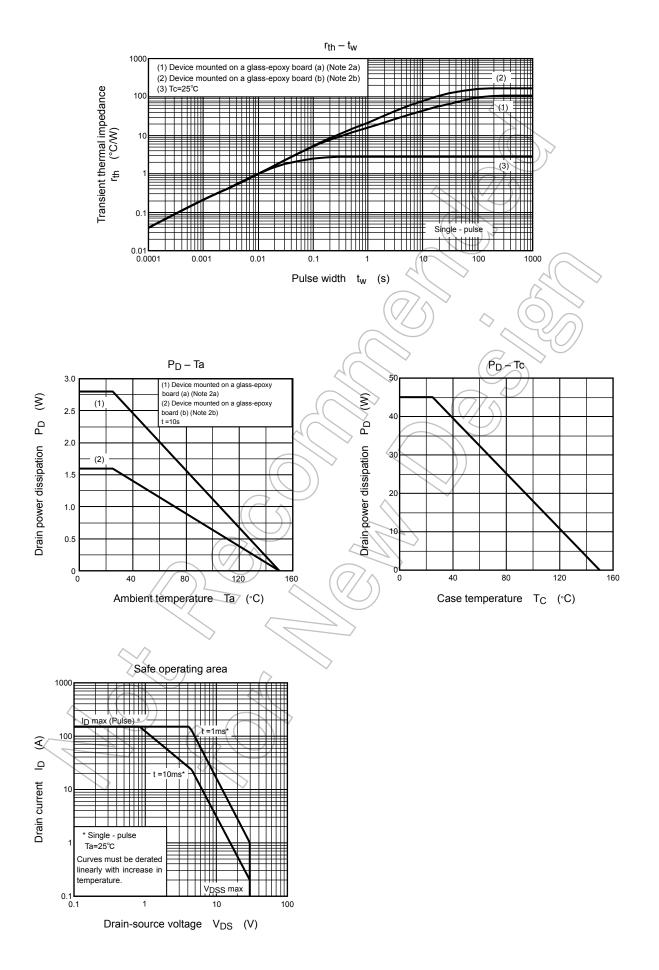




Total gate charge Qg



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